

SURFACE PASSIVATION TO REDUCE DARK CURRENT IN A CMOS IMAGE SENSOR

Abstract

A method for reducing dark current in a photodiode is disclosed. The photodiode comprises a N-well formed in a P-substrate. The method comprises doping the surface of said N-well with a nitrogen dopant. Alternatively, an oxygen or silicon dopant may be used. Still alternatively, a silicon oxynitride layer may be formed over the N-well.